

(Withdrawn) 1. A method for preparing a photoresist layer for e-beam inspection comprising:

5 out-gassing said photoresist layer whereby an outgas from said photoresist layer during said e-beam inspection is substantially prevented.

(Withdrawn) 2. The method for of claim 1 wherein:

10 said step of out-gassing said photoresist layer further comprising a step of implanting ions into said photoresist layer to activate an out-gassing from said photoresist layer.

(Withdrawn) 3. A method for preparing a photoresist layer for e-beam inspection comprising:

15 increasing a conductivity of said photoresist layer whereby electric charging of said photoresist layer during said e-beam inspection is substantially prevented.

20 (Withdrawn) 4. The method for of claim 3 wherein:

25 said step of increasing a conductivity of said photoresist layer further comprising a step of implanting conductive ions into said photoresist layer to increase a conductivity of said photoresist layer.

(Withdrawn) 5. The method for of claim 3 wherein:

30 said step of increasing a conductivity of said photoresist layer further comprising a step of implanting carbon ions into said photoresist layer.

(Withdrawn) 6. The method for of claim 3 wherein:

5                   said step of increasing a conductivity of said photoresist  
layer further comprising a step of implanting indium ions  
into said photoresist layer.

(Withdrawn) 7. The method for of claim 3 wherein:

10                   said step of increasing a conductivity of said photoresist  
layer further comprising a step of implanting Sb ions into  
said photoresist layer.

(Withdrawn) 8. The method for of claim 3 wherein:

15                   said step of increasing a conductivity of said photoresist  
layer further comprising a step of implanting silicon ions  
into said photoresist layer.

(Withdrawn) 9. The method for of claim 3 wherein:

20                   said step of increasing a conductivity of said photoresist  
layer further comprising a step of implanting metallic ions  
into said photoresist layer.

25                   (Withdrawn) 10. The method for of claim 3 wherein:

30                   said step of increasing a conductivity of said photoresist  
layer further comprising a step of implanting a conductive  
ions at an implanting energy approximately 1000 ev into  
said photoresist layer.

(Withdrawn) 11. The method for of claim 3 wherein:

5                   said step of increasing a conductivity of said photoresist layer further comprising a step of implanting a conductive ions having an ion dosage in a approximate range  $10^{16}$  /cm<sup>2</sup> to  $10^{18}$  /cm<sup>2</sup> into said photoresist layer.

(Withdrawn) 12. The method for of claim 3 wherein:

10                   said step of increasing a conductivity of said photoresist layer further comprising a step of plasma immersing ion implant a conductive ions into said photoresist layer.

(Withdrawn) 13. The method for of claim 3 further comprising:

15                   out-gassing said photoresist layer whereby an outgas from said photoresist layer during said e-beam inspection is substantially prevented.

20                   (Withdrawn) 14. The method for of claim 13 wherein:

                    said step of out-gassing said photoresist layer further comprising a step of implanting ions into said photoresist layer to activate an out-gassing from said photoresist layer.

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(Original ) 15. A photoresist layer for integrated circuit manufacture processed for e-beam inspection comprising:

30                   an out-gas content less than 0.5 percents thus substantially prevent out-gassing from said photoresist layer during said e-beam inspection.

(Original ) 16. A photoresist layer for integrated circuit manufacture processed for e-beam inspection comprising:

5 an electric resistivity less than  $2000 \text{ ohm/cm}^2$  thus substantially prevent an electric charging of said photoresist layer during said e-beam inspection.

(Original ) 17. A photoresist layer for integrated circuit manufacture comprising:

10 implanted conductive ions for increasing a conductivity of said photoresist layer.

(Original ) 18. The photoresist layer for of claim 17 wherein:

15 said implanted conductive ions further comprising implanted carbon ions.

(Original ) 19. The photoresist layer for of claim 17 wherein:

20 said implanted conductive ions further comprising implanted indium ions.

(Original ) 20. The photoresist layer for of claim 17 wherein:

25 said implanted conductive ions further comprising implanted Sb ions.

(Original ) 21. The photoresist layer for of claim 17 wherein:

30 said implanted conductive ions further comprising implanted silicon ions.

(Original ) 22. The photoresist layer for of claim 17 wherein:

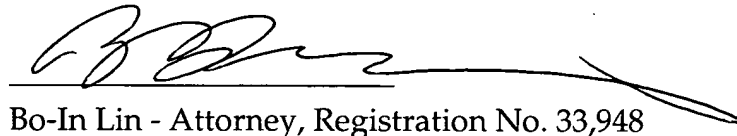
said implanted conductive ions further comprising  
implanted metallic ions.

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Respectfully submitted  
Daniel Tang and Jiong Chen et al.

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By



Bo-In Lin - Attorney, Registration No. 33,948  
13445 Mandoli Drive, Los Altos Hills, CA 94022  
(650) 949-0418 (Tel), (650) 949-4118 (Fax)

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July 21, 2005